



VND05B VND05B (011Y) / VND05B (012Y)

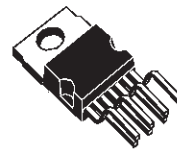
DOUBLE CHANNEL HIGH SIDE SMART POWER SOLID STATE RELAY

TYPE	V _{DSS}	R _{DS(on)}	I _n (*)	V _{CC}
VND05B	40V	200mΩ	1.6A	26 V
VND05B (011Y)				
VND05B (012Y)				

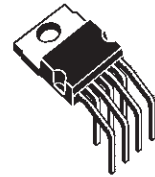
- OUTPUT CURRENT (CONTINUOUS): 9A AT T_c=85°C PER CHANNEL
- 5V LOGIC LEVEL COMPATIBLE INPUT
- THERMAL SHUT-DOWN
- UNDERVOLTAGE PROTECTION
- OPEN DRAIN DIAGNOSTIC OUTPUT
- INDUCTIVE LOAD FAST DEMAGNETIZATION
- VERY LOW STAND-BY POWER DISSIPATION

DESCRIPTION

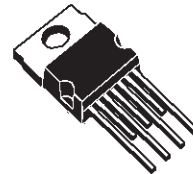
The VND05B, VND05B (011Y), VND05B (012Y) is a monolithic device designed in STMicroelectronics VIPower technology, intended for driving resistive or inductive loads with one side connected to ground. This device has two channels, and a common diagnostic. Built-in thermal shutdown protects the chip from overtemperature and short circuit. The status output provides an indication of open load in on state, open load in off state, overtemperature conditions and stuck-on to V_{CC}.



HEPTAWATT
(vertical)



HEPTAWATT
(horizontal)

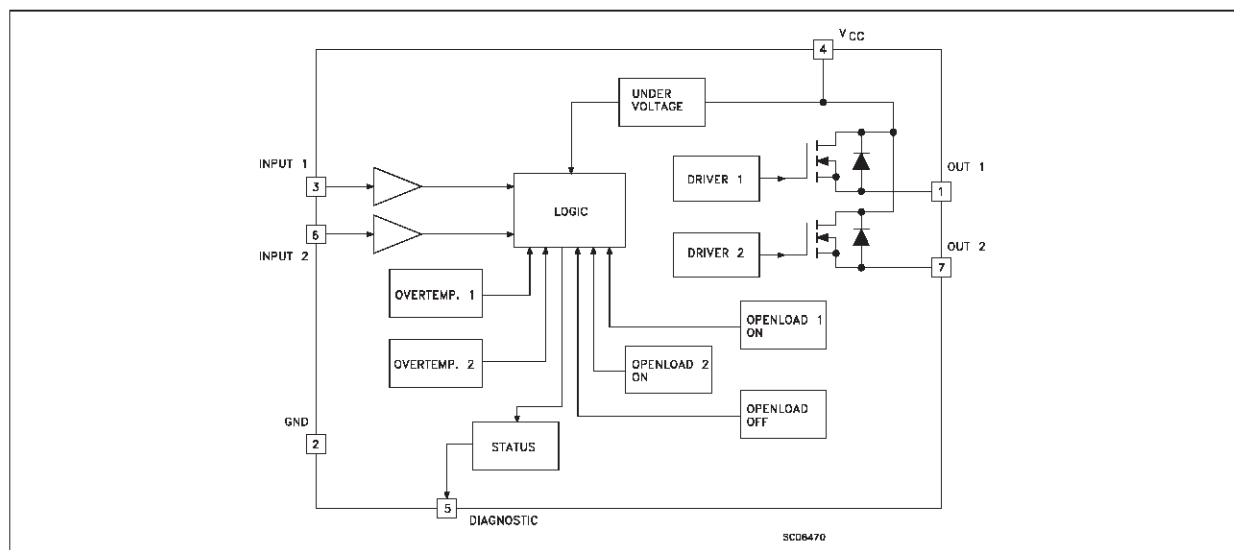


HEPTAWATT
(in-line)

ORDER CODES

HEPTAWATT vertical	VND05B
HEPTAWATT horizontal	VND05B (011Y)
HEPTAWATT in-line	VND05B (012Y)

BLOCK DIAGRAM



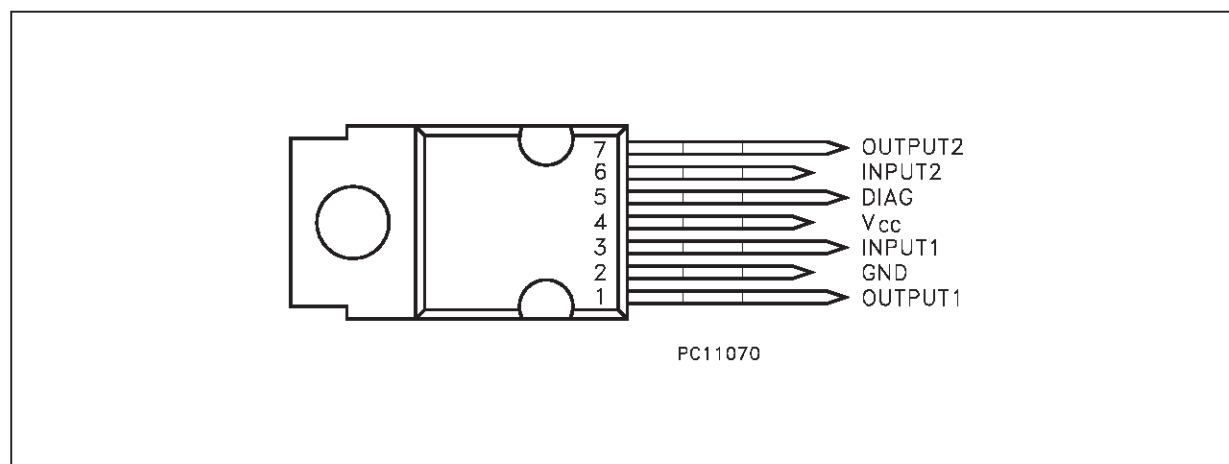
(*) I_n= Nominal current according to ISO definition for high side automotive switch (see note 1)

VND05B / VND05B (011Y) / VND05B (012Y)

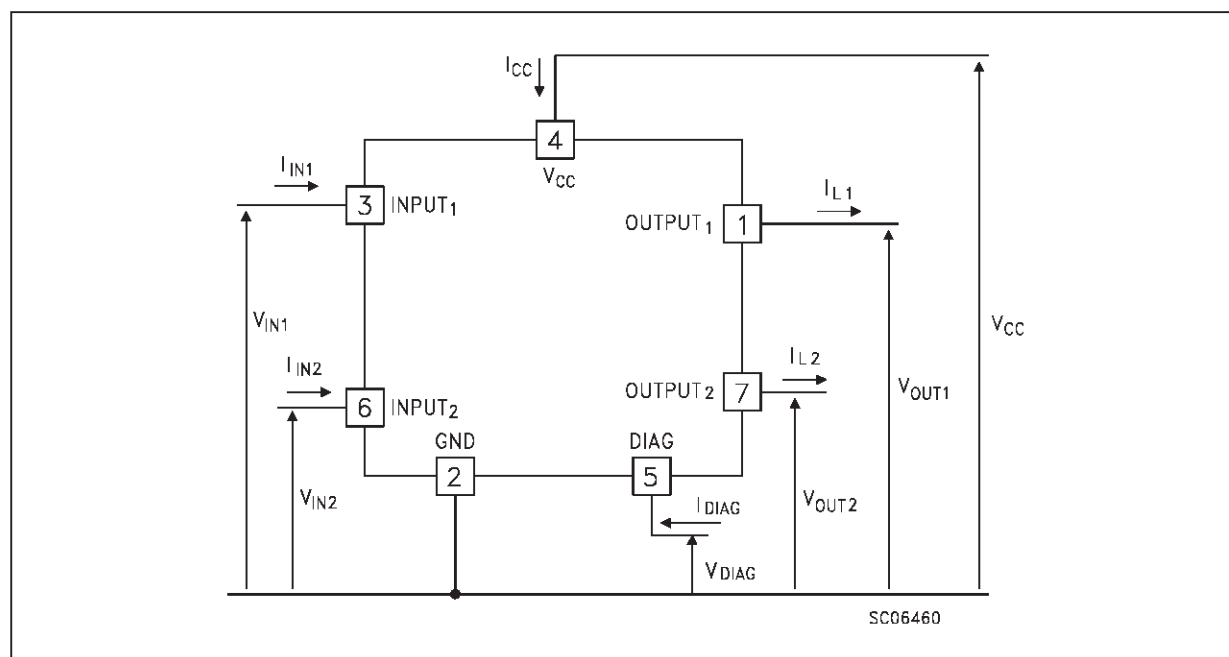
ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
$V_{(BR)DSS}$	Drain-Source breakdown voltage	40	V
I_{OUT}	Output current (continuous) at $T_c=85^\circ\text{C}$	9	A
$I_{OUT(RMS)}$	RMS Output current at $T_c=85^\circ\text{C}$ and $f > 1\text{Hz}$	9	A
I_R	Reverse output current at $T_c=85^\circ\text{C}$	-9	A
I_{IN}	Input current	+/- 10	mA
$-V_{CC}$	Reverse supply voltage	-4	V
I_{STAT}	Status current	+/- 10	mA
V_{ESD}	Electrostatic discharge ($R=1.5\text{k}\Omega$, $C=100\text{pF}$)	2000	V
P_{TOT}	Power dissipation at $T_c=25^\circ\text{C}$	59	W
T_j	Junction operating temperature	-40 to 150	$^\circ\text{C}$
T_{STG}	Storage temperature	-55 to 150	$^\circ\text{C}$

CONNECTION DIAGRAM TOP VIEW



CURRENT AND VOLTAGE CONVENTIONS



THERMAL DATA

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case (MAX)	2.1	°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient (MAX)	60	°C/W

ELECTRICAL CHARACTERISTICS (8V<V_{CC}<16V; -40°C≤T_j≤125°C; unless otherwise specified)

POWER

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V _{CC}	Supply voltage		6	13	26	V
I _n (*)	Nominal current	T _c =85°C; V _{DS(on)} ≤0.5V; V _{CC} =13V	1.6		2.6	A
R _{ON}	On state resistance	I _{OUT} =I _n ; V _{CC} =13V; T _j =25°C	0.13		0.2	Ω
I _S	Supply current	Off state; T _j =25°C; V _{CC} =13V		35	100	μA
V _{DS(MAX)}	Maximum voltage Drop	I _{OUT} =7.5A; T _j =85°C; V _{CC} =13V	1.44		2.3	V
R _i	Output to GND internal impedance	T _j =25°C	5	10	20	KΩ

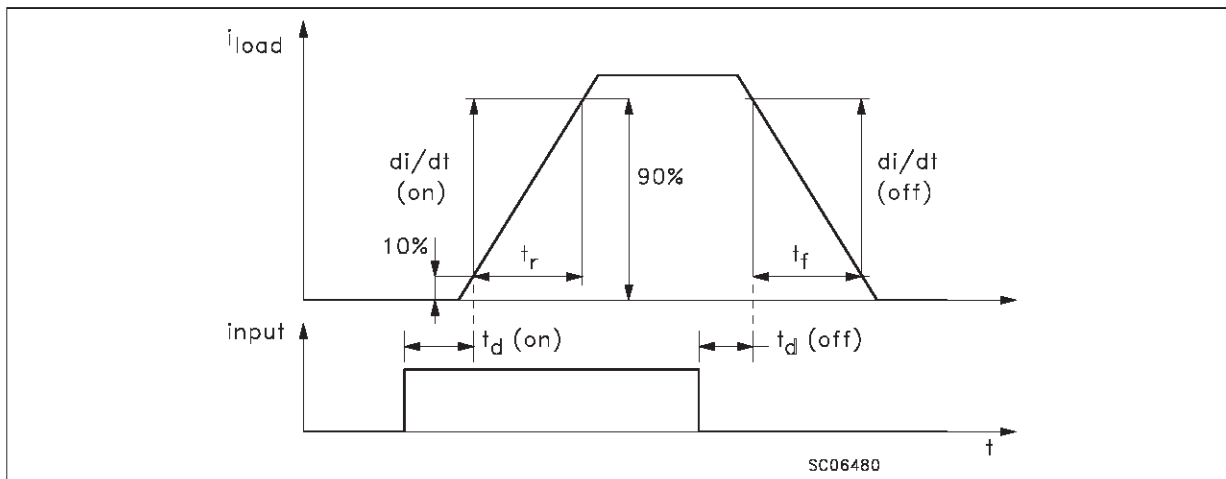
SWITCHING

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
t _{d(on)} (^)	Turn-on delay time of output current	R _{OUT} =5.4Ω	5	25	200	μs
t _r (^)	Rise time of output current	R _{OUT} =5.4Ω	10	50	180	μs
t _{d(off)} (^)	Turn-off delay time of output current	R _{OUT} =5.4Ω	10	75	250	μs
t _f (^)	Fall time of output current	R _{OUT} =5.4Ω	10	35	180	μs
(di/dt) _{on}	Turn-on current slope	R _{OUT} =5.4Ω	0.003		0.1	A/μs
(di/dt) _{off}	Turn-off current slope	R _{OUT} =5.4Ω	0.005		0.1	A/μs

LOGIC INPUT

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V _{IL}	Input low level voltage				1.5	V
V _{IH}	Input high level voltage		3.5		(•)	V
V _{I(hyst)}	Input hysteresis voltage		0.2	0.9	1.5	V
I _{IN}	Input current	V _{IN} =5V; T _j =25°C		30	100	μA
V _{ICL}	Input clamp voltage	I _{IN} =10mA I _{IN} =-10mA	5	6 -0.7	7	V V

Switching Time Waveforms



FUNCTIONAL DESCRIPTION

The device has a common diagnostic output for both channels which indicates open load in on-state, open load in off-state, overtemperature conditions and stuck-on to V_{CC} .

From the falling edge of the input signal, the status output, initially low to signal a fault condition (overtemperature or open load on-state), will go back to a high state with a different delay in case of overtemperature (t_{povl}) and in case of open load (t_{pol}) respectively. This feature allows to discriminate the nature of the detected fault. To protect the device against short-circuit and overcurrent condition, the thermal protection turns the integrated PowerMOS off at a minimum junction temperature of 140°C. When this temperature returns to 125°C the switch is automatically turned in again. In short-circuit the protection reacts with virtually no delay, the sensor (one for each channel) being located inside each of the two PowerMOS areas. This positioning allows the device to operate with one channel in automatic thermal cycling and the other one on a normal load. An internal function of the devices ensures the fast demagnetization of inductive loads with a typical voltage (V_{demag}) of -18V. This function allows to greatly reduce the power dissipation according to the formula:

$$P_{dem} = 0.5 \cdot L_{load} \cdot (I_{load})^2 \cdot [(V_{CC} + V_{demag}) / V_{demag}] \cdot f$$

where f = switching frequency and

V_{demag} = demagnetization voltage.

The maximum inductance which causes the chip temperature to reach the shutdown temperature in a specified thermal environment is a function of the load current for a fixed V_{CC} , V_{demag} and f according to the above formula. In this device if the GND pin is disconnected, with V_{CC} not exceeding 16V, both channels will switch off.

PROTECTING THE DEVICE AGAINST REVERSE BATTERY

The simplest way to protect the device against a continuous reverse battery voltage (-26V) is to insert a Schottky diode between pin 2 (GND) and ground, as shown in the typical application circuit (fig. 2).

The consequences of the voltage drop across this diode are as follows:

- If the input is pulled to power GND, a negative voltage of $-V_f$ is seen by the device. (V_{il} , V_{ih} thresholds and V_{STAT} are increased by V_f with respect to power GND).
- The undervoltage shutdown level is increased by V_f .

If there is no need for the control unit to handle external analog signals referred to the power GND, the best approach is to connect the reference potential of the control unit to the device ground (see application circuit in fig. 3), which becomes the common signal GND for the whole control board avoiding shift on V_{il} , V_{ih} and V_{STAT} . This solution allows the use of a standard diode.

THRUTH TABLE

		INPUT 1	INPUT 2	OUTPUT 1	OUTPUT 2	DIAGNOSTIC
Normal operation		L	L	L	L	H
		H	H	H	H	H
		L	H	L	H	H
		H	L	H	L	H
Undervoltage		X	X	L	L	H
Thermal shutdown	Channel 1	H	X	L	X	L
	Channel 2	X	H	X	L	L
Openload	Channel 1	H	X	H	X	L
		L	L	L	L	L
	Channel 2	X	H	X	H	L
		L	L	L	L	L
Output shorted to V _{CC}	Channel 1	H	X	H	X	L
		L	L	H	L	L
	Channel 2	X	H	X	H	L
		L	L	L	H	L

Figure 1: Waveforms

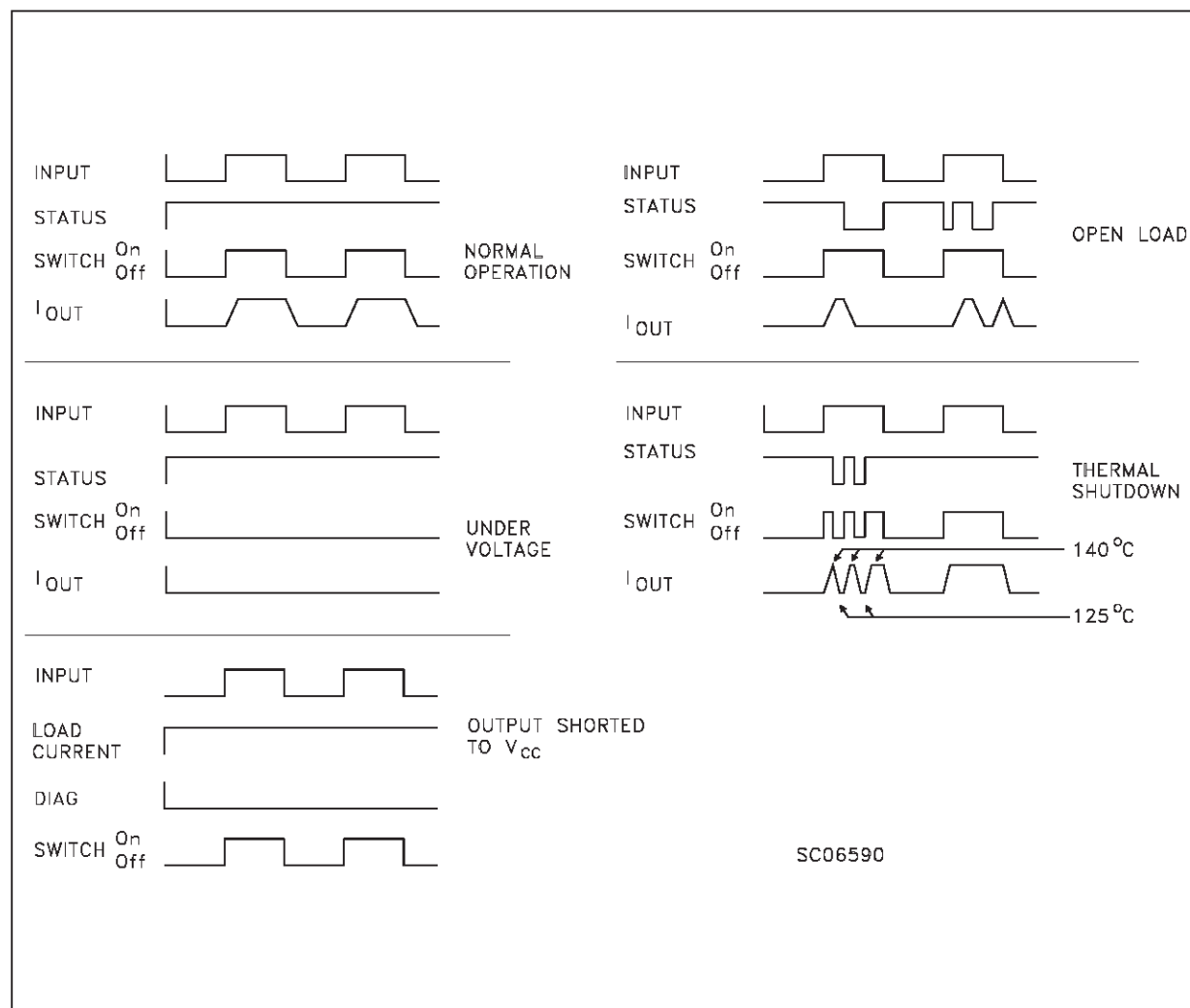


Figure 2: Typical application circuit with a Schottky diode for reverse supply protection

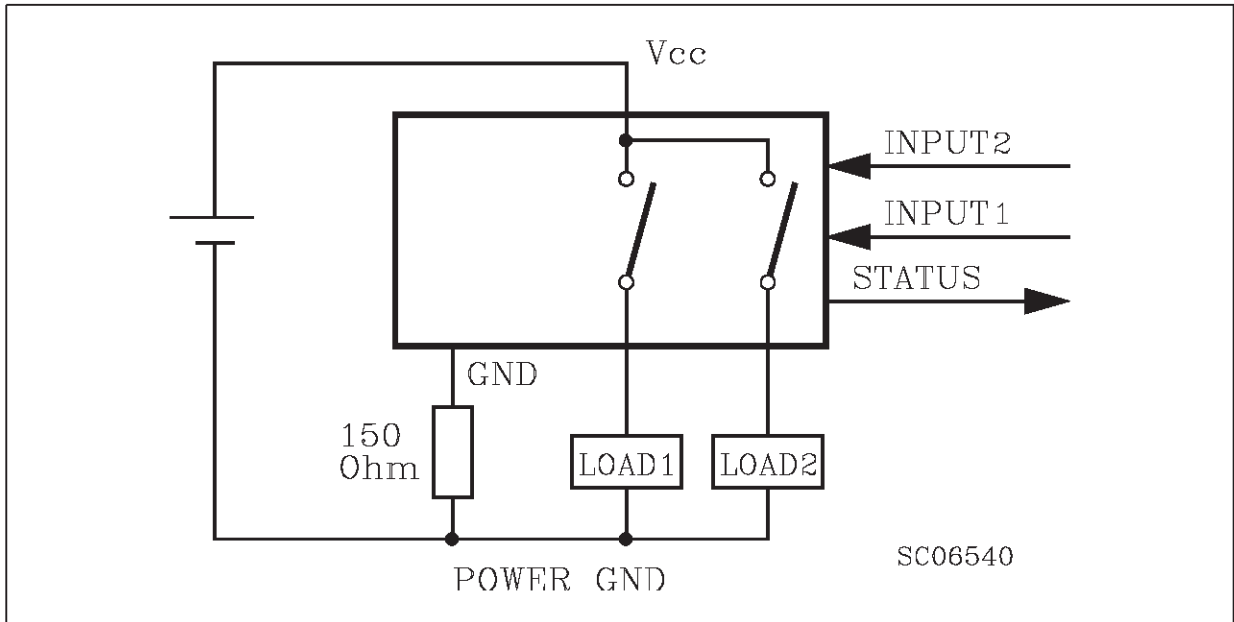
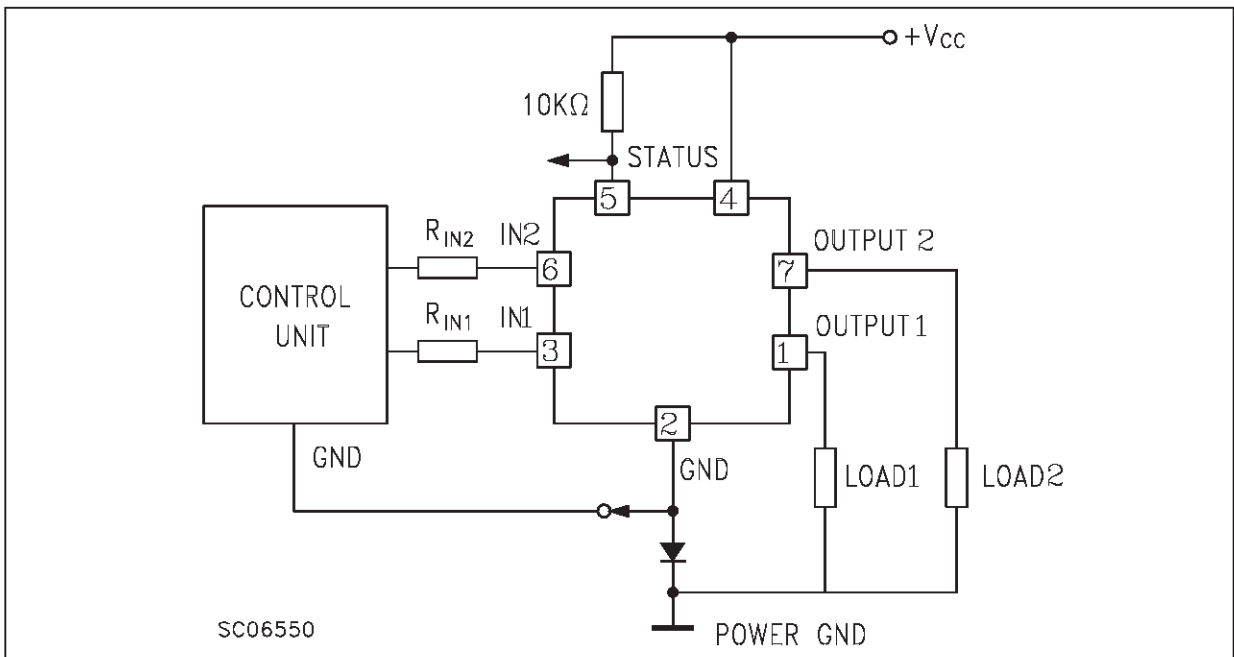
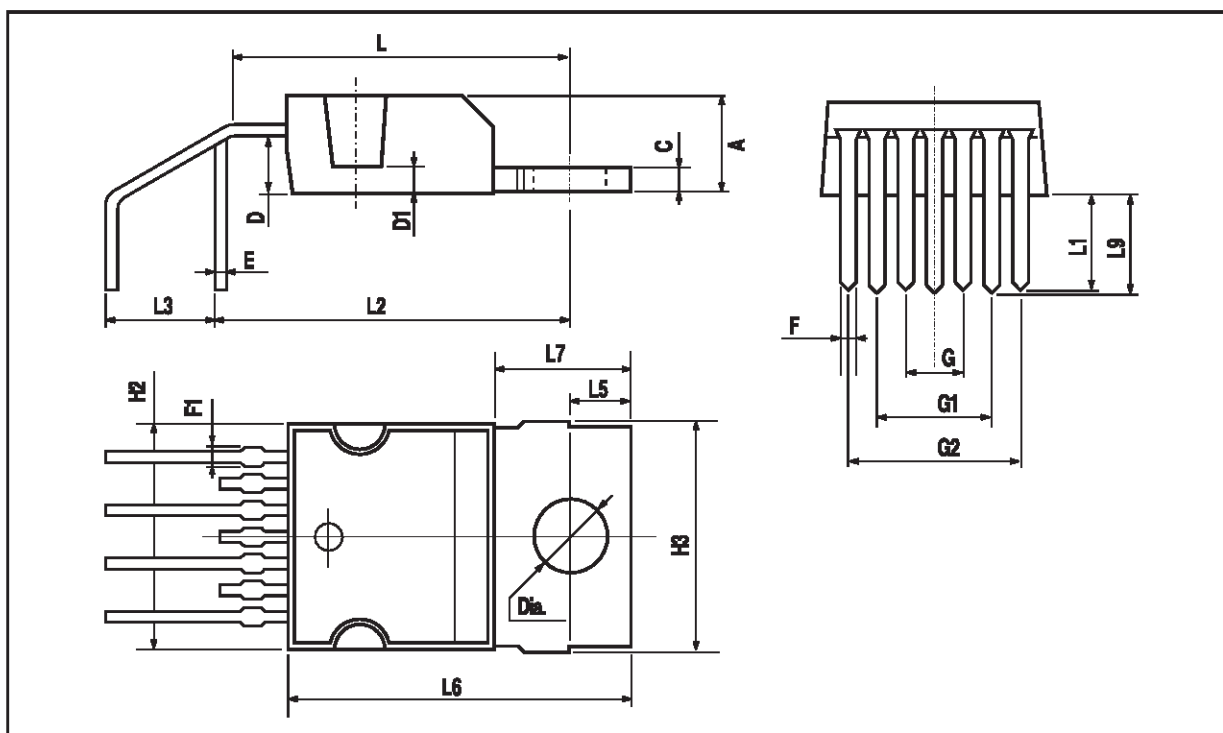


Figure 3: Typical application circuit with separate signal ground



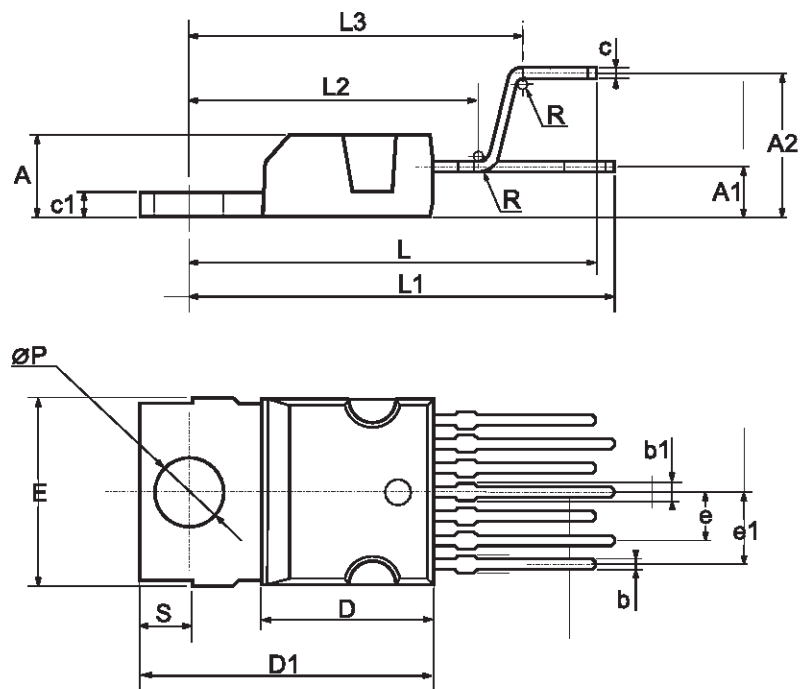
HEPTAWATT (horizontal) MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			4.8			0.189
C			1.37			0.054
D	2.4		2.8	0.094		0.110
D1	1.2		1.35	0.047		0.053
E	0.35		0.55	0.014		0.022
F	0.6		0.8	0.024		0.031
F1			0.9			0.035
G	2.41	2.54	2.67	0.095	0.100	0.105
G1	4.91	5.08	5.21	0.193	0.200	0.205
G2	7.49	7.62	7.8	0.295	0.300	0.307
H2			10.4			0.409
H3	10.05		10.4	0.396		0.409
L		14.2			0.559	
L1		4.4			0.173	
L2		15.8			0.622	
L3		5.1			0.201	
L5	2.6		3	0.102		0.118
L6	15.1		15.8	0.594		0.622
L7	6		6.6	0.236		0.260
L9		4.44			0.175	
Dia	3.65		3.85	0.144		0.152



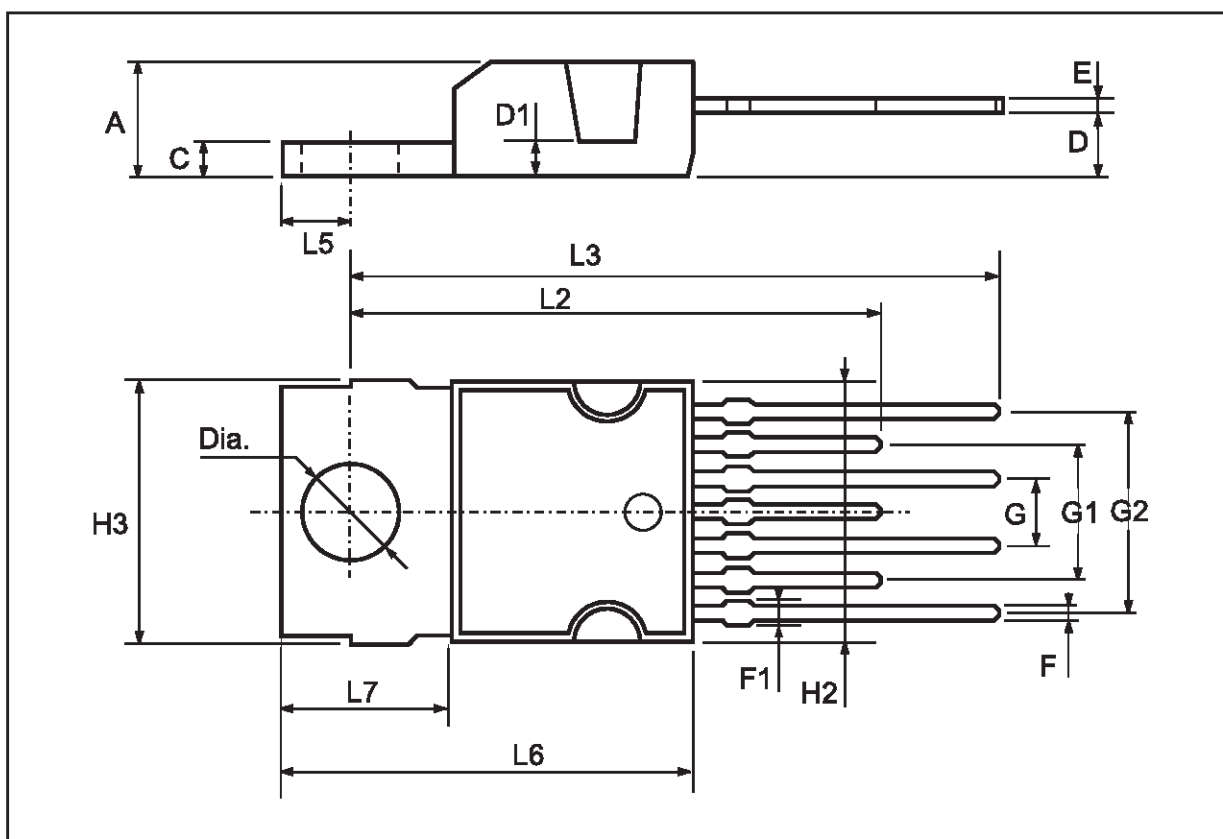
HEPTAWATT (vertical) MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			4.8			0.189
C			1.37			0.054
D	2.4		2.8	0.094		0.110
D1	1.2		1.35	0.047		0.053
E	0.35		0.55	0.014		0.022
F	0.6		0.8	0.024		0.031
F1			0.9			0.035
G	2.41	2.54	2.67	0.095	0.100	0.105
G1	4.91	5.08	5.21	0.193	0.200	0.205
G2	7.49	7.62	7.8	0.295	0.300	0.307
H2			10.4			0.409
H3	10.05		10.4	0.396		0.409
L		16.97			0.668	
L1		14.92			0.587	
L2		21.54			0.848	
L3		22.62			0.891	
L5	2.6		3	0.102		0.118
L6	15.1		15.8	0.594		0.622
L7	6		6.6	0.236		0.260
M		2.8			0.110	
M1		5.08			0.200	



HEPTAWATT (in-line) MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			4.8			0.189
C			1.37			0.054
D	2.4		2.8	0.094		0.110
D1	1.2		1.35	0.047		0.053
E	0.35		0.55	0.014		0.022
F	0.6		0.8	0.024		0.031
F1			0.9			0.035
G	2.41	2.54	2.67	0.095	0.100	0.105
G1	4.91	5.08	5.21	0.193	0.200	0.205
G2	7.49	7.62	7.8	0.295	0.300	0.307
H2			10.4			0.409
H3	10.05		10.4	0.396		0.409
L2	22.4		22.9	0.882		0.902
L3	25.4		26	1.000		1.024
L5	2.6		3	0.102		0.118
L6	15.1		15.8	0.594		0.622
L7	6		6.6	0.236		0.260
Dia.	3.65		3.85	0.144		0.152



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